

YJGD20G10A

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FOR NEW DESIGN



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NMOS(Die1/Die2) Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$			1	
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$			100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250$	1.0	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=15A$		17	22	m
		$V_{GS}=4.5V, I_D=7A$		21	27	
Diode Forward Voltage	V_{SD}	$I_S=20A, V_{GS}=0V$		0.96	1.3	V
Maximum Body-Diode Continuous Current	I_S				20	A
Gate Resistance	R_g	$f=1MHz$		1.2		
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V, f=1MHz$		1051		pF
Output Capacitance	C_{oss}			399		
Reverse Transfer Capacitance	C_{rss}			18		
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=50V, I_D=10A$		16		nC
Gate-Source Charge	Q_{gs}			5.6		
Gate-Drain Charge	Q_{gd}			2.4		
Reverse Recovery Charge	Q_{rr}	$I_r=20A, di/dt=100A/us$		42		ns
Reverse Recovery Time	t_{rr}			39.8		
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=50V, I_D=4.0A$ $R_{GEN}=3.0$		39.2		ns
Turn-on Rise Time	t_r			11		
Turn-off Delay Time	$t_{D(off)}$			53.2		

Turn-off fall Time



NMOS(Die1/Die2) Typical Performance Characteristics

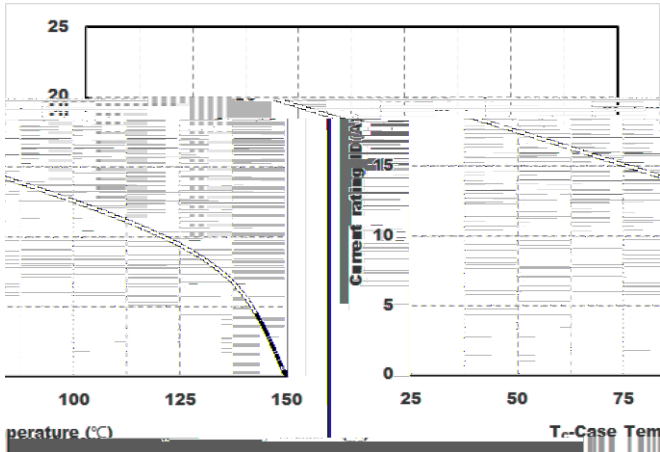


Figure7. Drain current

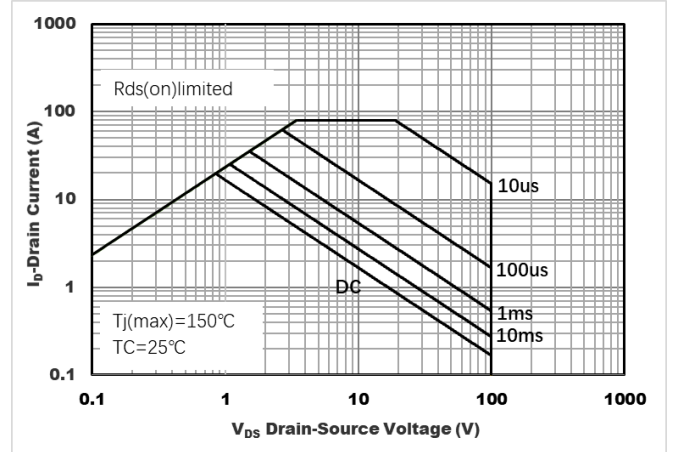


Figure8.Safe Operation Area

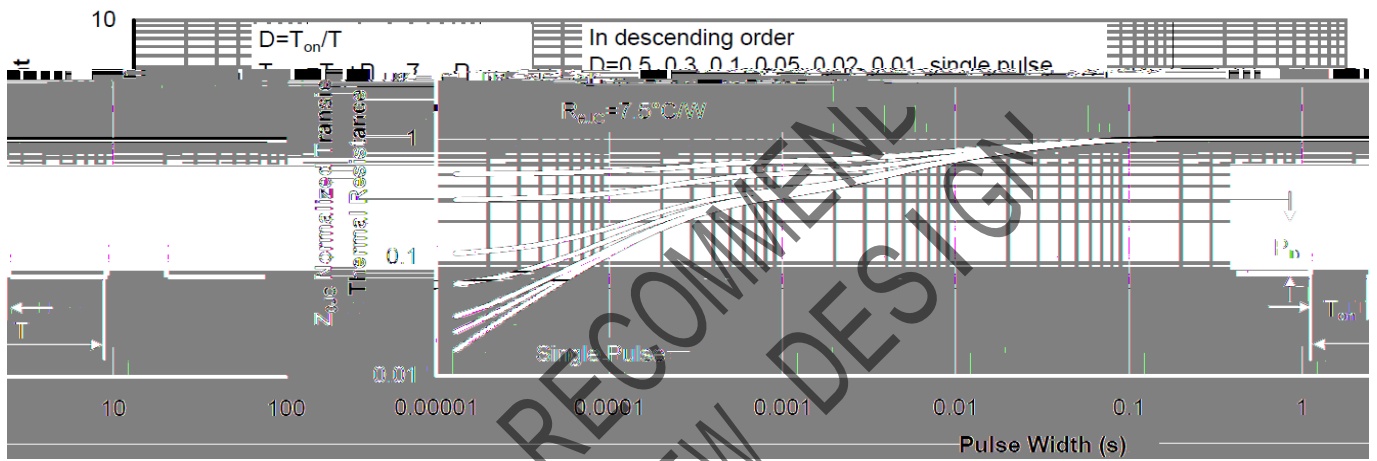
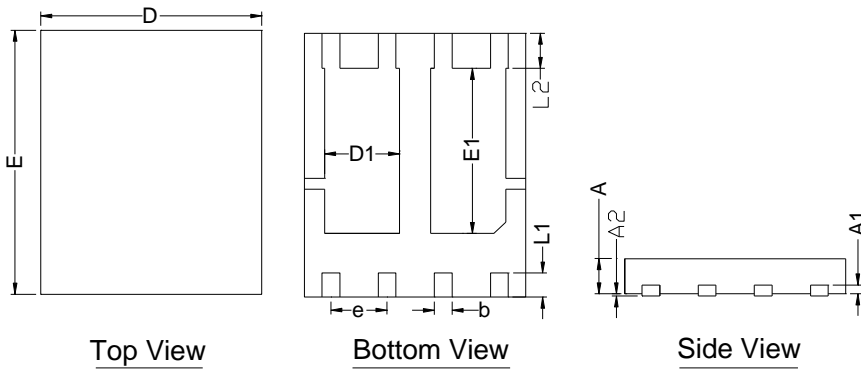


Figure9.Normalized Maximum Transient thermal impedance

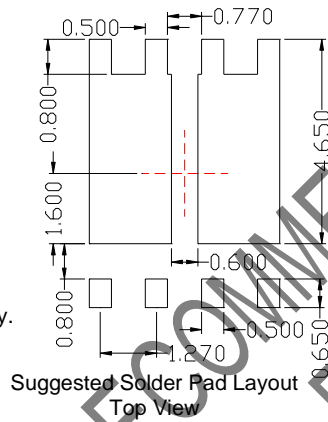


DFN5060-8L Package information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	4.90	5.00	5.10
E	5.90	6.00	6.10
A	0.70	0.80	0.90
A1	0.20 BSC		
A2			0.10
D1	1.60	1.70	1.80
E1	3.65	3.75	3.85
L1	0.45	0.55	0.65
L2	0.80 BSC		
b	0.30	0.40	0.50
e	1.27 BSC		

- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.10\text{mm}$.
 3. The pad layout is for reference purposes only.



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